Ultra low losses
Passivation: Silicon Oxide

V_{RRM} = 1200V
I_F = 100A
Die Size: 8.0 x 8.0mm

Maximum rated values:

Parameter	Symbol	Min	Max	Unit
Repetitive peak reverse voltage	V_{RRM}	-	1200	V
Working Peak Reverse Voltage	V_{RWM}	-	1200	V
DC Blocking Voltage	V_R	-	1200	V
Continuous forward current	I_F	-	100	A
Repetitive peak forward current* (Square Wave, 20 kHz)	I_{FRM}	-	200	A
Nonrepetitive Peak Surge Current (Halfwave, 1 Phase, 60 Hz)	I_{FSM}	-	tbd	A
Avalanche Energy	E_{AVL}	-	tbd	mj
Junction temperature	T_j	-	150	°C
Operating and Storage Temperature	T_{STG}, T_J		-65 to 175	°C

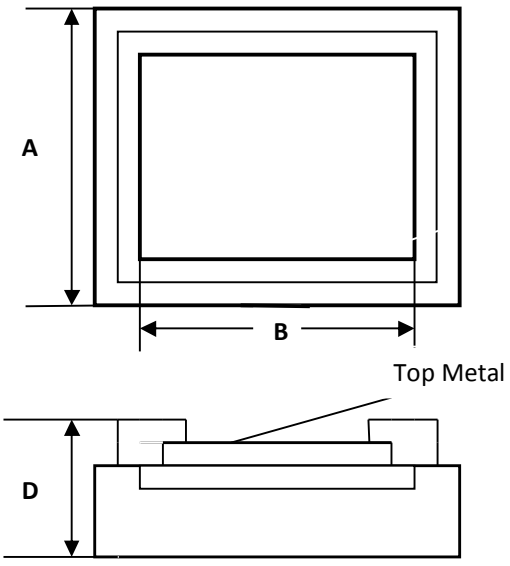
*- Limited by T_{vj} max

Diode Characteristics values:

Parameter	Symbol	Conditions		Min	Typ	Max	Unit
Continuous forward voltage	V_F	I_F=100A, T_{vj}=25°C		-	1.9	2.1	V
Continuous forward voltage	V_F	I_F=100A, T_{vj}=150°C		-	1.85	2.0	V
Continuous reverse current	I_R	V_R=1200V	T_{vj}=25°C	-	10	40	uA
			T_{vj}=125°C	-	1.5	2.0	mA
Peak reverse recovery current	I_{RRM}	I_F=100A, V_R=700V, dI_F/dt=200A/uS		-	tbd		A
Recovered charge	Q_{RR}			-	tbd		µC
Reverse Recovery Time	t_{rr}			-	tbd		nS
	ta			-	tbd		
	tb			-	tbd		
Reverse Recovery Time	t_{rr}	I_F=1A, V_R=30V, dI_F/dt=200A/uS		-	75	90	nS

Mechanical properties:

*Top metal: **Al-Ti** – for Wire Bonding*
*Backside metal: **Ti-Ni-Ag** – for Soldering*



DIM	ITEM	µm
A_X A_Y	Die Size	8000 8000
D	Thickness	350 max
Scribe Line Width		60